## IMPERIAL COLLEGE LONDON

DEPARTMENT OF ELECTRICAL AND ELECTRONIC ENGINEERING **EXAMINATIONS 2017** 

EEE PART II: MEng, BEng and ACGI

Corrected copy

## **ANALOGUE ELECTRONICS 2**

Thursday, 15 June 10:00 am

Time allowed: 2:00 hours

There are THREE questions on this paper.

Answer ALL questions. Q1 carries 40% of the marks. Questions 2 and 3 carry equal marks (30% each).

Any special instructions for invigilators and information for candidates are on page 1.

Examiners responsible

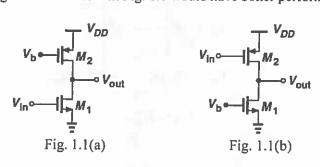
First Marker(s):

T. Constandinou

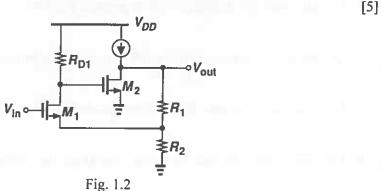
Second Marker(s): C. Toumazou



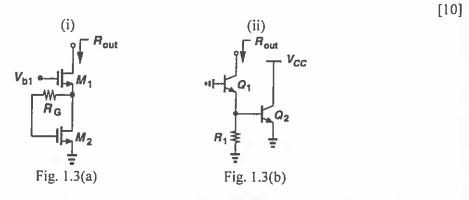
- 1. This question consists of 5 sub-questions. Each item can be answered in a few words or a short paragraph with use of a diagram and/or expression where helpful. Please answer all sub-questions and simplify expressions where possible stating any assumptions made.
  - a) Which of the topologies shown below in Fig. 1.1 would have better performance? Explain why.



- b) Propose a *circuit topology* (e.g. common source amplifier with resistive load), for each of the following applications, in each case justifying your selection, and sketching the circuit schematic.
  - (i) A pre-amplifier to interface to a capacitive microphone. [5]
  - (ii) A circuit to increase the DC level of a signal by 1V. [5]
  - (iii) A high frequency amplifier providing relatively high isolation between the input and output. [5]
- c) An inverting amplifier must provide a nominal gain of 20 with a gain error of 0.5%. Determine the minimum required op-amp gain.
- d) Determine the closed loop gain of the circuit shown below in Fig. 1.2. Assume  $\lambda = 0$ .



e) Derive expressions (by inspection) for the *output resistance* of the amplifier circuits shown below in Fig. 1.3 (including  $r_0$ ).



2. The circuit shown below in Fig. 2.1 is a single-stage fully differential amplifier with corresponding transistor dimensions shown in Table 2.1.

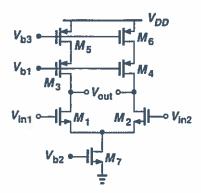


Fig. 2.1

Table 2.1. Transistor sizes

$M_1$	M <sub>2</sub>	<i>M</i> <sub>3</sub>	M <sub>4</sub>	M <sub>5</sub>	<i>M</i> <sub>6</sub>	$M_7$
200/0.5	200/0.5	9/0.18	9/0.18	50/1	50/1	50/1

Assume all devices are in saturation and assume  $\lambda \neq 0$ . Use the following expression for the large signal drain current of a MOSFET (in saturation) with corresponding transistor parameters:

$$I_D = \frac{1}{2}\mu C_{ox} \frac{W}{L} (V_{GS} - V_{TH})^2$$

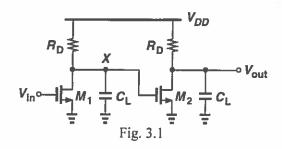
$$\begin{array}{lll} \mu_n C_{ox} = 200 \mu A/V^2 & V_{THN} = 0.4 V & \lambda_N = 0.1 V^{-1} \\ \mu_p C_{ox} = 100 \mu A/V^2 & V_{THP} = -0.5 V & \lambda_P = 0.2 V^{-1} \end{array}$$

- a) Design a voltage reference circuit to generate  $V_{b2}$  from a 1.8V supply such that  $I_{D7} = 2\text{mA}$ . [5]
- b) Determine an expression for the differential voltage gain of the amplifier.

  [5]
- c) Determine an expression for the common-mode voltage gain of the amplifier.

  [5]
- d) Use your answers to parts (b) and (c) to evaluate the common-mode rejection ratio. [10]
- e) State the function of transistors  $M_1 M_2$ ,  $M_3 M_4$ ,  $M_5 M_6$ , and  $M_7$  and comment on the specified device sizes. [5]

3. The circuit below in Fig. 3.1 illustrates a cascade of two identical common source stages.



- a) Neglecting channel-length modulation and other capacitances, construct the Bode plot of  $V_{out}/V_{in}$  including both the magnitude and phase responses. [8]
- b) Annotate your plot with the following: (i) Bandwidth; (ii) Phase margin; (iii) Gain Margin. [5]
- c) Derive the transfer function of the circuit, substitute  $s = j\omega$ , and obtain an expression for  $|V_{out}/V_{in}|$ . Determine the -3dB bandwidth of the circuit. [10]
- d) Using your answers to parts (b) and (c), design the two-stage amplifier for a total voltage gain of 15 and -3dB bandwidth of 1.8GHz. Assume each stage carries a bias current of 1mA, CL=40fF, and  $\mu_n C_{ox} = 200 \mu A/V^2$ . [7]

